



## Bias Circuit

## Background of the Invention

The present invention relates to a bias circuit,  
5 and particularly to a bias circuit capable of outputting  
a bias current that depends on current amplification  
gains  $\beta$  of transistors and resistance values without  
depending on the accuracy of a required reference voltage.

A conventional bias circuit comprises an NMOS  
10 transistor for constant current source (hereinafter  
called "a constant current source transistor") 2 whose  
constant current value is controlled based on the output  
of a feedback amplifier, a differential pair of NMOS  
transistors (hereinafter called "differential  
15 transistors") equal in dimension from each other, which  
is connected to the drain of the constant current source  
transistor, diode-connected load PMOS transistors  
(hereinafter called "load transistors") respectively  
connected to the drains of the differential transistors,  
20 current mirror PMOS transistors (hereinafter called  
"mirror transistors") which constitute the load  
transistor and a current mirror, and a resistor 9 which  
receives a current that flows through the mirror  
transistor. The drain side of the mirror transistor  
25 serves as a current output terminal.

Different reference voltages are respectively  
applied to the gates of the differential transistors, and

another reference voltage is further applied to a positive input terminal of the feedback amplifier.

When, for example, the differential transistors are increased in current amplification gain  $\beta$  due to variations in manufacture in such a bias circuit, the feedback amplifier controls a current flowing through the constant current source transistor so as to be reduced. Accordingly, the mirror transistor outputs an output current that depends on the current amplification gains  $\beta$  of the differential transistors and the resistance value of the resistor.

The conventional bias circuit is accompanied by a problem that the accuracy of the reference voltages applied to the differential transistors is degraded, and when an input potential difference varies, the output current also varies eventually.

#### Summary of the Invention

The present invention may provide a bias circuit capable of outputting an output current which does not depend on the accuracy of each reference voltage.

The bias circuit of the present invention comprises a current source MOS transistor, a differential MOS transistor pair for dividing a current flowing through the current source MOS transistor on a differential basis, load MOS transistors that respectively receive respective one currents flowing through the differential MOS

transistors, current mirror MOS transistors constituting the load MOS transistor and a current mirror, a first resistive element for converting a current flowing through the current mirror MOS transistor into a voltage, and an amplifier for controlling the current source MOS transistor in such a manner that the voltage converted by the first resistive element becomes a second reference voltage.

10                      **Brief Description of the Drawings**

While the specification concludes with claims particularly pointing out and distinctly claiming the subject matter which is regarded as the invention, it is believed that the invention, the objects and features of the invention and further objects, features and advantages thereof will be better understood from the following description taken in connection with the accompanying drawings in which:

Fig. 1 shows a bias circuit according to a first embodiment of the present invention;

Fig. 2 illustrates a bias circuit according to a second embodiment of the present invention;

Fig. 3 depicts a bias circuit according to a third embodiment of the present invention;

Fig. 4 shows a bias circuit according to a fourth embodiment of the present invention; and

Fig. 5 illustrates a bias circuit according to a

fifth embodiment of the present invention.

#### Detailed Description of the Preferred Embodiments

Preferred embodiments of the present invention will  
5 hereinafter be described in detail with reference to the  
accompanying drawings.

Fig. 1 shows a bias circuit according to a first  
embodiment of the present invention.

The bias circuit according to the first embodiment  
10 of the present invention comprises an NMOS transistor for  
constant current source (hereinafter called "a constant  
current source transistor") 2 whose constant current  
value  $I_2$  is controlled based on the output of a feedback  
amplifier 1, a differential pair of NMOS transistors  
15 (hereinafter called "differential transistors") 3 and 4  
different in dimension from each other, which is  
connected to the drain of the constant current source  
transistor 2, diode-connected load PMOS transistors  
(hereinafter called "load transistors") 5 and 6  
20 respectively connected to the drains of the differential  
transistors 3 and 4, current mirror PMOS transistors  
(hereinafter called "mirror transistors") 7 and 8 which  
constitute the load transistor 6 and a current mirror,  
and a resistor 9 which receives a current that flows  
25 through the mirror transistor 7. The drain side of the  
mirror transistor 8 serves as a current output terminal  
OUT.

A point VR where the drain of the mirror transistor 7 and the resistor 9 are connected to each other, is connected to a negative input terminal of the feedback amplifier 1.

5 Assuming that the dimensions of the differential transistors 3 and 4 are represented as, for example: W/L of differential transistor 3: W/L of differential transistor 4 = 1 : N (where N is an integer greater than or equal to 2), it makes it easy to realize the bias  
10 circuit according to the present embodiment.

The operation of the bias circuit according to the first embodiment of the present invention will next be described. As distinct from the conventional bias circuit, no input potential difference  $\Delta V$  exists in the bias  
15 circuit according to the first embodiment of the present invention. However, the dimensions of the differential transistors 3 and 4 are made different to thereby make it possible to cause a difference input voltage to generate an offset. Eventually, a differential input voltage  $\Delta V'$   
20 occurs between a gate voltage of the differential transistor 3 and a gate voltage of the differential transistor 4, whereby the present bias circuit performs an operation equivalent to that of the conventional bias circuit.

25 Namely, a current  $I_4$  that flows through the differential transistor 4 is represented as follows:

$$I_4 = I_2/2 - (\beta/4 \cdot W/L) \Delta V' \cdot \{ (2 \cdot I_2) / (\beta/2 \cdot W/L) - \Delta V'^2 \} \quad (2)$$

Incidentally, the introduction of above equation (2) will be explained in detail.

$$I_3 = (\beta/2 \cdot W/L) \cdot (V_{gs3} - V_t)^2 \quad (a)$$

$$I_4 = (\beta/2 \cdot W/L) \cdot (V_{gs4} - V_t)^2 \quad (b)$$

$$5 \quad I_3 + I_4 = 2I_d \quad (c)$$

$$I_3 - I_4 = \Delta I_d \quad (d)$$

Finding the square root of (a) and (b) and subtracting both from each other results in the following equation:

$$10 \quad I_3 - I_4 = (\beta/2 \cdot W/L) \Delta V'^2 \quad (e)$$

Raising (c) and (d) to the second power and subtracting both from each other results in the following equation:

$$2 \cdot (I_3 \cdot I_4) = \{ (2I_d)^2 - \Delta I_d^2 \} \quad (f)$$

15 Raising (e) to the second power and substituting (f) therein results in the following equation:

$$\Delta I_d = (\beta/2 \cdot W/L) \Delta V' \cdot \{ (2 \cdot I_2) / (\beta/2 \cdot W/L) - \Delta V'^2 \} \quad (g)$$

Taking (c) - (d) results in the following equation:

$$I_4 = I_d - \Delta I_d/2 \quad (h)$$

20 Since  $2I_d = I_2$  in the present embodiment, (h) is rewritten as follows:

$$I_4 = I_2/2 - \Delta I_d/2 \quad (i)$$

Eventually, the equation (i) is rewritten as follows:

$$25 \quad I_4 = I_2/2 - (\beta/4 \cdot W/L) \Delta V' \cdot \{ (2 \cdot I_2) / (\beta/2 \cdot W/L) - \Delta V'^2 \} \quad (j)$$

The current of the mirror transistor 7 is represented as  $I_7 = I_4$ , and the potential at the

connecting point VR is represented as  $V_r = R \cdot I_4$ . The feedback amplifier 1 controls the current I2 of the constant current source transistor so that the VR reaches VREF3.

5           Also the feedback amplifier 1 controls the current I12 of the constant current source transistor such that the potential Vr at the connecting point VR reaches VREF3.

          Further, when the current amplification gains  $\beta$  of the differential transistors 3 and 4 become large due to  
10 variations in manufacture or the like, for example, I3 and I4 also increase. With their current increases, the potential ~~Vr at the connecting point VR~~ also becomes high. Therefore, the feedback amplifier 1 controls the current I2 of the constant current source transistor 2 as small  
15 as practicable to lower the potential Vr so as to reach  $V_r = VREF3$ . Consequently, the mirror transistor 8 outputs an output current I8 that depends on the current amplification gains  $\beta$  of the differential transistors 3 and 4 and the resistance value of the resistor 9.

20           As described above, the bias circuit according to the first embodiment of the present invention makes the dimensions of differential transistors different and applies the same reference voltage to their gates, thereby making it possible to output an output current  
25 that depends on the current amplification gains  $\beta$  of transistors and the resistance value without depending on the accuracy of the reference voltage.

Fig. 2 illustrates a bias circuit according to a second embodiment of the present invention.

The bias circuit according to the second embodiment of the present invention has a configuration wherein the resistor 9 employed in the bias circuit according to the first embodiment is substituted with a so-called external resistor 10 external to the outside of a semiconductor chip.

The absolute resistance value of the resistor 9 lying within the semiconductor chip varies according to variations in manufacture (about  $\pm 10\%$  in general).

-----Since the accuracy of the absolute resistance value of the external resistor 10 is generally about  $\pm 1\%$ , the dependence of an output current  $I_8$  on the resistance value can be significantly suppressed owing to the use of such an external resistor. The utilization of the external resistor is particularly effective for a case in which the output current  $I_8$  is needed which depends only on current amplification gains  $\beta$  of differential transistors 3 and 4.

In a manner similar to the bias circuit according to the first embodiment, the bias circuit according to the second embodiment of the present invention as described above makes the dimensions of differential transistors different and applies the same reference voltage to their gates, thereby making it possible to output an output current that depends only on current



amplification gains  $\beta$  of transistors without depending on the accuracy of the reference voltage.

Fig. 3 shows a bias circuit according to a third embodiment of the present invention.

5           The bias circuit according to the second embodiment of the present invention has a configuration wherein the reference voltage VREF3 employed in the bias circuit according to the first embodiment is substituted with VREF1.

10           Thus, the number of reference voltages necessary for the bias circuit according to the third embodiment may be one, and hence the bias circuit becomes apt to be realized.

          In addition to the advantageous effect of the bias  
15   circuit according to the first embodiment, the bias circuit according to the third embodiment of the present invention as described above makes identical a reference voltage of a feedback amplifier and a reference voltage for differential transistors to thereby allow the  
20   required number of reference voltages to be set to one. It is thus possible to make it easy to realize a bias circuit.

Fig. 4 shows a bias circuit according to a fourth embodiment of the present invention.

25           The bias circuit according to the fourth embodiment of the present invention comprises an NMOS transistor for constant current source (hereinafter called "a constant

current source transistor") 2 whose constant current value  $I_2$  is controlled based on the output of a feedback amplifier 1, a differential pair of NMOS transistors (hereinafter called "differential transistors") 3 and 4 equal in dimension from each other, which is connected to the drain of the constant current source transistor 2, load resistors 5 and 6 respectively connected to the drains of the differential transistors 3 and 4, and a mirror transistor 13 which is controlled in accordance with the output of the feedback amplifier 1 in a manner similar to the constant current source transistor 2 and whose drain side serves as a current output terminal.

In a manner similar to the first embodiment, a reference voltage  $V_{REF1}$  is applied to the gates of the differential transistors 3 and 4, and  $V_{REF3}$  is applied to a positive input terminal of the feedback amplifier 1.

A point where the drain of the differential transistor 4 and the resistor 6 are connected to each other, is set as  $V_{R2}$  and connected to a negative input terminal of the feedback amplifier 1.

The other terminals of the load resistors 5 and 6 are both connected to  $V_{DD}$ .

In a manner similar to the first embodiment, a current  $I_4$  that flows through the differential transistor 4 is expressed in the above equation (2), and a current that flows through the load resistor 6 is equal to that of the differential transistor 4. Eventually, the

potential at the connecting point VR2 results in  $V_{r2} = V_{DD} - R \cdot I_4$ .

The feedback amplifier 1 controls the current  $I_2$  of the constant current source transistor so that the potential  $V_{r2}$  becomes  $V_{REF3}$ . Eventually, the mirror transistor 13 outputs an output current  $I_{13}$  that depends on the current amplification gains  $\beta$  of the differential transistors 3 and 4, the resistance value of the resistor 6 and  $V_{DD}$ .

In addition to the advantageous effect of the bias circuit according to the first embodiment, the bias circuit according to the fourth embodiment of the present invention as described above makes use of resistors whose one ends are connected to  $V_{DD}$ , thereby making it possible to output an output current that depends on current amplification gains  $\beta$  of transistors, resistance values and  $V_{DD}$  without the accuracy of a reference voltage.

Fig. 5 shows a bias circuit according to a fifth embodiment of the present invention.

The bias circuit according to the fifth embodiment of the present invention has a configuration wherein a dummy transistor 14 is provided in addition to the differential transistors 3 and 4 employed in the bias circuit according to the first embodiment.

The source of the dummy transistor 14 is connected to the drain of a constant current source transistor 2 but the drain thereof is being floated. Also a reference

voltage VREF1 is applied to the gate of the dummy transistor 14 in a manner similar to the differential transistors 3 and 4.

Since the differential transistors 3 and 4 are  
5 different in dimension when the bias circuit of the present invention is laid out, there is a possibility that matching accuracy will be degraded.

Therefore, the dummy transistor 14 is placed on the differential transistor 3 side small in dimension, and  
10 the differential transistors 3 and 4 and the dummy transistor 14 are laid out symmetrically.

It is thus possible to reduce a production mismatch between the differential transistors 3 and 4 and to obtain an output current I8 less reduced in variation  
15 from a mirror transistor 8.

As described above, the bias circuit according to the fifth embodiment of the present invention adds a dummy transistor to the differential transistor employed in the bias circuit according to the first embodiment,  
20 thereby making it possible to reduce a manufacturing mismatch between the differential transistors and obtain an output current that depends on current amplification gain  $\beta$  of each transistor small in variation, and a resistance value.

25 While the present invention has been described with reference to the illustrative embodiments, this description is not intended to be construed in a limiting

sense. Various modifications of the illustrative  
embodiments, as well as other embodiments of the  
invention, will be apparent to those skilled in the art  
on reference to this description. It is therefore  
5 contemplated that the appended claims will cover any such  
modifications or embodiments as fall within the true  
scope of the invention.